

Issue Date: 6 July 2015

Title of Change:	Update Notice of IPCN20626XF to modify the qualification plan due to typo error.		
Proposed first ship date:	30 October 2015		
Contact information:	Contact your local ON Semiconductor Sales Office or < Yasuhiro Igarashi @onsemi.com>		
Samples:	Contact your local ON Semiconductor Sales Office		
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or < Kazutoshi.Kitazume@onsemi.com>.		
Type of notification:	ON Semiconductor will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact <pcn.support@onsemi.com>.</pcn.support@onsemi.com>		
Change category:	□ Wafer Fab Change		
Change Sub-Category(s):          □ Datasheet/Product Doc change         □ Datasheet/Product Doc change         □ Shipping/Packaging/Marking         □ Other:         Other: Sites Affected:			
All site(s) not app		onductor site(s) :  External Fou	indry/Subcon site(s)
Description and Purpose:			
Modification of the read point of te	emperature from 100 to 5	00cycles and pressure cooker from 50 to 96hrs.	
Test		Conditions	Read point
Steady State Operating Life		Tj=150degC	1000 hrs.
High Temperature Reverse Bias		Ta=150degC,VR=max	1000 hrs.
Temp Humidity Storage		Ta=85degC, RH=85%	1000 hrs.
Temperature Cycle		Ta=-55degC to 150degC 30min each	500 cycles
Pressure Cooker		Ta=121degC,2.03×10 <sup>5</sup> Pa,100%	96 hrs.
High Temperature Storage		Ta-1E0dagC	
High Temperature Storage		Ta=150degC	1000 hrs.
Resistance to Soldering heat(Refle	ow)	Solder Temp.:260degC±5degC	1000 hrs. 10s
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